Unit: mm

TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL IGBT

GT15Q301

HIGH POWER SWITCHING APPLICATIONS MOTOR CONTROL APPLICATIONS

• Third-generation IGBT

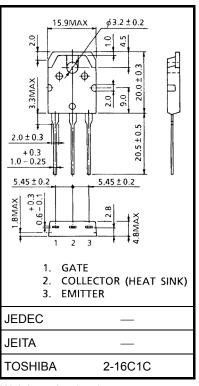
• Enhancement mode type

High speed : t_f = 0.32 µs (Max.)
 Low saturation voltage : VCE (sat) = 2.7 V (Max.)

• FRD included between emitter and collector

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC | | SYMBOL | RATING | UNIT | |
|---|-----|------------------|---------|------|--|
| Collector-Emitter Voltage | | V _{CES} | 1200 | ٧ | |
| Gate-Emitter Voltage | | V _{GES} | ±20 | ٧ | |
| Collector Current | DC | IC | 15 | Α | |
| | 1ms | I _{CP} | 30 | Α | |
| Emitter-Collector Forward Current | DC | lF | 15 | Α | |
| | 1ms | I _{FM} | 30 | Α | |
| Collector Power Dissipation (Tc = 25°C) | | P _C | 170 | W | |
| Junction Temperature | | Tj | 150 | °C | |
| Storage Temperature Range | | T _{stg} | -55~150 | °C | |



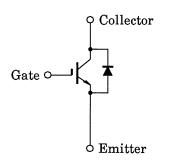
Weight: 4.6 g (typ.)

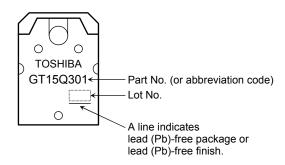
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

EQUIVALENT CIRCUIT

MARKING

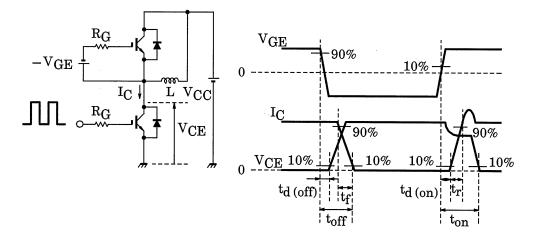


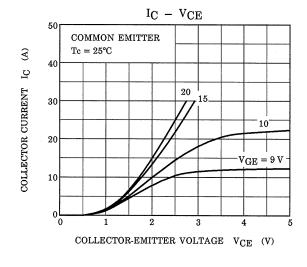


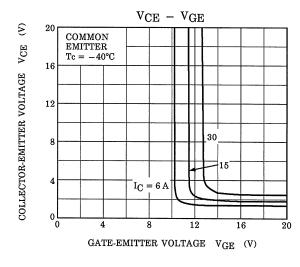
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

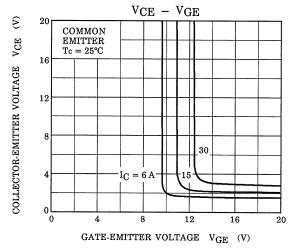
| CHARACTERISTIC | | SYMBOL | TEST CONDITION | MIN | TYP. | MAX | UNIT |
|------------------------------|--------------------|-----------------------|--|-----|------|------|--------|
| Gate Leakage Current | | I _{GES} | V _{GE} = ±20 V, V _{CE} = 0 | _ | _ | ±500 | nA |
| Collector Cut-Off Current | | I _{CES} | V _{CE} = 1200 V, V _{GE} = 0 | - | _ | 1.0 | mA |
| Gate-Emitter Cut-Off Voltage | | V _{GE} (OFF) | I _C = 1.5 mA, V _{CE} = 5 V | 4.0 | _ | 7.0 | V |
| Collector-Emitter S | Saturation Voltage | V _{CE} (sat) | (sat) I _C = 15 A, V _{GE} = 15 V | | 2.1 | 2.7 | V |
| Input Capacitance | | C _{ies} | V _{CE} = 50 V, V _{GE} = 0, f = 1 MHz | _ | 950 | _ | pF |
| Switching Time | Rise Time | t _r | Inductive Load V_{CC} = 600 V, I_{C} = 15 A V_{GG} = ±15 V, R_{G} = 56 Ω (Note) | _ | 0.05 | _ | - μs |
| | Turn-On Time | t _{on} | | _ | 0.12 | _ | |
| | Fall Time | t _f | | - | 0.16 | 0.40 | |
| | Turn-Off Time | t _{off} | | - | 0.56 | _ | |
| Peak Forward Volta | age | V _F | I _F = 15 A, V _{GE} = 0 | - | _ | 3.0 | V |
| Reverse Recovery Time | | t _{rr} | I _F = 15 A, di / dt = -200 A / μs | _ | _ | 350 | ns |
| Thermal Resistance (IGBT) | | R _{th (j−c)} | _ | _ | _ | 0.74 | °C / W |
| Thermal Resistance (Diode) | | R _{th (j−c)} | _ | _ | _ | 1.56 | °C / W |

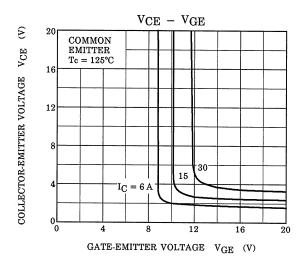
Note: Switching time measurement circuit and input / output waveforms

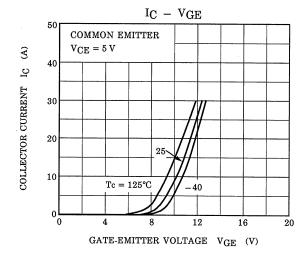


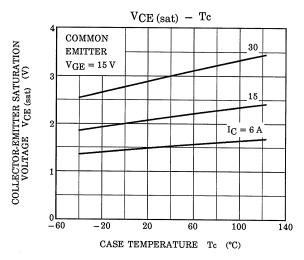




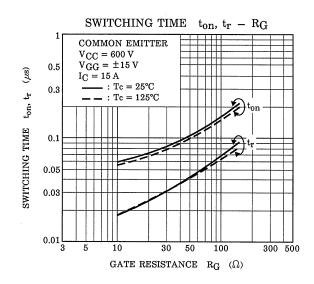


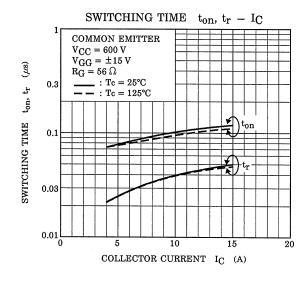


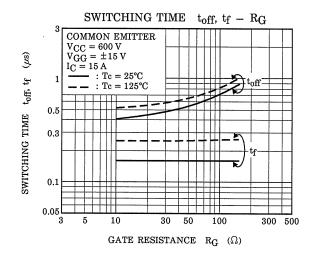


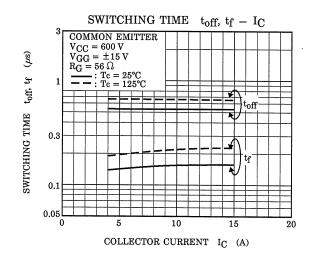


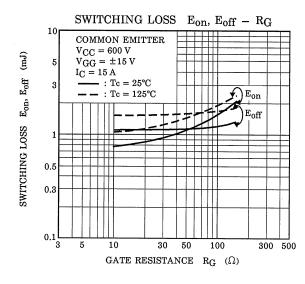
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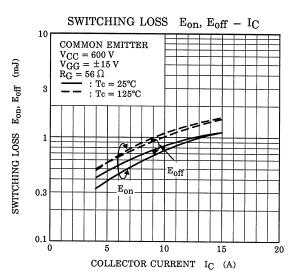


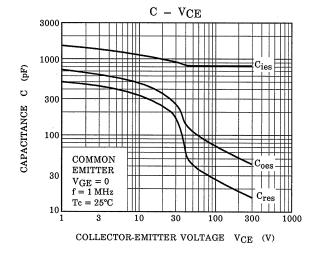


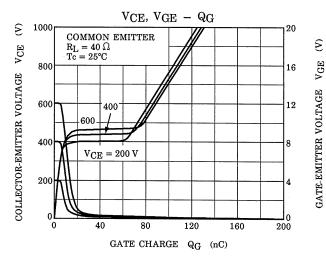


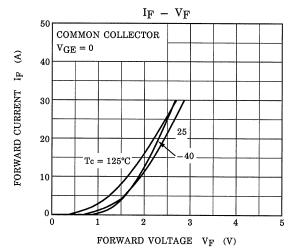


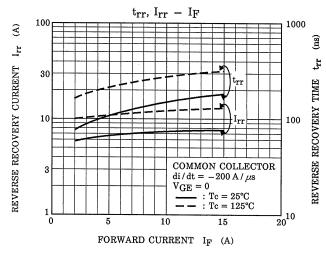


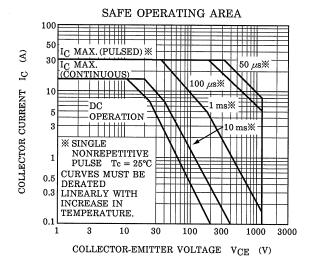


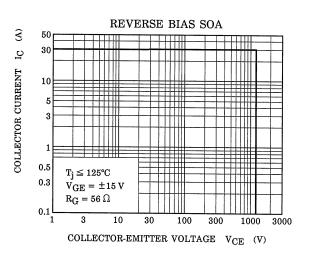




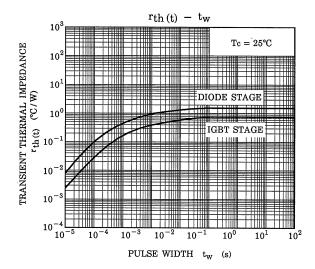








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